

Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	59
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2136asdfa-30

Table 1.2 Specifications (2)

Item	Function	Description
Serial interface	UART0_0 and UART0_1	2 channels Clock synchronous serial I/O mode, clock asynchronous serial I/O mode
	UART2	1 channel Clock synchronous serial I/O mode, clock asynchronous serial I/O mode, I ² C mode (I ² C-bus), multiprocessor communication mode
Clock Synchronous serial interface	(SSU) SSU_0	1 channel (also used for the I ² C bus)
	(I ² C bus) I ² C_0	1 channel (also used for the SSU)
LIN module	HW-LIN_0	Hardware LIN 1 channel (timer RJ_0, UART0_0, or UART0_1 used)
A/D converter		Resolution: 10 bits × 12 channels, sample and hold function, sweep mode
Comparator B		2 circuits
Touch Sensor control unit (TSCU)		System CH × 4, electrostatic capacitive touch detection × 28
CRC calculator		CRC-CCITT ($X^{16} + X^{12} + X^5 + 1$), CRC-16 ($X^{16} + X^{15} + X^2 + 1$) compliant
Flash memory		• Program/erase voltage: VCC = 2.7 V to 5.5 V • Program/erase endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • BGO (background operation) function (data flash)
Operating frequency/ Power supply voltage		CPU clock = 20 MHz (VCC = 2.7 V to 5.5 V) CPU clock = 5 MHz (VCC = 1.8 V to 5.5 V)
Current consumption		Typ. 6.5 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 4.0 μA (VCC = 3.0 V, wait mode f(XCIN) = 32 kHz) Typ. 2.2 μA (VCC = 3.0 V, stop mode)
Operating ambient temperature		-20°C to 85°C (N version) -40°C to 85°C (D version) ⁽¹⁾
Package		64-pin LQFP Package code: PLQP0064KB-A (previous code: 64P6Q-A) Package code: PLQP0064GA-A (previous code: 64P6U-A)

Note:

1. Specify the D version if it is to be used.

1.4 Pin Assignment

Figure 1.3 shows Pin Assignment (Top View). Tables 1.4 to 1.6 list the Pin Name Information by Pin Number.

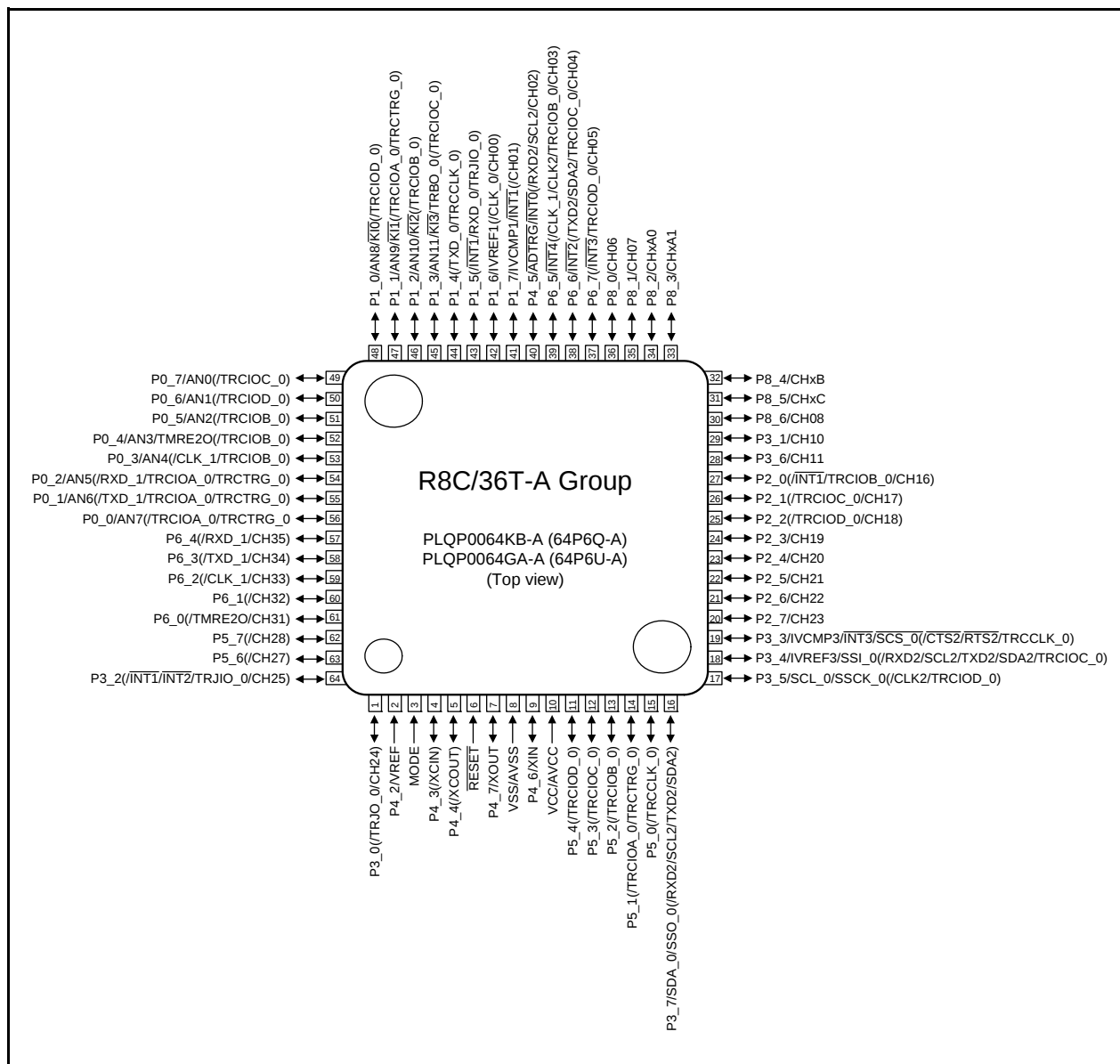


Figure 1.3 Pin Assignment (Top View)

Table 1.6 Pin Name Information by Pin Number (Timer RC, Timer RE2, and Others)

Port	Pin No.	Timer RC						Timer RE2	Others		
		TRCCLK_0	TRCIOA_0	TRCIOB_0	TRCIOC_0	TRCIOD_0	TRCTRG_0	TMRE2O			
P0_0	56		TRCIOA_0				TRCTRG_0		AN7		
P0_1	55		TRCIOA_0				TRCTRG_0		AN6		
P0_2	54		TRCIOA_0				TRCTRG_0		AN5		
P0_3	53			TRCIOB_0					AN4		
P0_4	52			TRCIOB_0				TMRE2O	AN3		
P0_5	51			TRCIOB_0					AN2		
P0_6	50					TRCIOD_0			AN1		
P0_7	49				TRCIOC_0				AN0		
P1_0	48					TRCIOD_0			AN8	K10	
P1_1	47		TRCIOA_0				TRCTRG_0		AN9	K11	
P1_2	46			TRCIOB_0					AN10	K12	
P1_3	45				TRCIOC_0				AN11	K13	
P1_4	44	TRCCLK_0									
P1_5	43										
P1_6	42								IVREF1		CH00
P1_7	41								IVCMP1		CH01
P2_0	27			TRCIOB_0							CH16
P2_1	26				TRCIOC_0						CH17
P2_2	25					TRCIOD_0					CH18
P2_3	24										CH19
P2_4	23										CH20
P2_5	22										CH21
P2_6	21										CH22
P2_7	20										CH23
P3_0	1										CH24
P3_1	29										CH10
P3_2	64										CH25
P3_3	19	TRCCLK_0							IVCMP3		
P3_4	18				TRCIOC_0				IVREF3		
P3_5	17					TRCIOD_0					
P3_6	28										CH11
P3_7	16										
P4_2	2								VREF		
P4_3	4								XCIN		
P4_4	5								XCOU		
P4_5	40								ADTRG		CH02
P4_6	9								XIN		
P4_7	7								XOUT		
P5_0	15	TRCCLK_0									
P5_1	14		TRCIOA_0				TRCTRG_0				
P5_2	13			TRCIOB_0							
P5_3	12				TRCIOC_0						
P5_4	11					TRCIOD_0					
P5_6	63										CH27
P5_7	62										CH28
P6_0	61							TMRE2O			CH31
P6_1	60										CH32
P6_2	59										CH33
P6_3	58										CH34
P6_4	57										CH35
P6_5	39			TRCIOB_0							CH03
P6_6	38				TRCIOC_0						CH04
P6_7	37					TRCIOD_0					CH05
P8_0	36										CH06
P8_1	35										CH07
P8_2	34										CHxA0
P8_3	33										CHxA1
P8_4	32										CHxB
P8_5	31										CHxC
P8_6	30										CH08

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 through R3.

R0 can be split into high-order (R0H) and low-order (R0L) registers to be used separately as 8-bit data registers. The same applies to R1H and R1L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). Similarly, R3 and R1 can be used as a 32-bit data register.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 functions in the same manner as A0. A1 can be combined with A0 and used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register used for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of a relocatable interrupt vector table.

2.5 Program Counter (PC)

PC is a 20-bit register that indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of the FLG register is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register used for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register that indicates the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated in the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. It must only be set to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0. Otherwise it is set to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value. Otherwise it is set to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow. Otherwise it is set to 0.

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts. Interrupts are disabled when the I flag is 0, and are enabled when the I flag is 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is 0. USP is selected when the U flag is 1. The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction for a software interrupt numbered from 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns eight processor interrupt priority levels from 0 to 7. If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

The write value must be 0. The read value is undefined.

Table 3.3 SFR Information (3) ⁽¹⁾

Address	Symbol	Register Name	After Reset	Remarks
0007Ah				
0007Bh				
0007Ch				
0007Dh				
0007Eh				
0007Fh				
00080h	U0MR_0	UART0_0 Transmit/Receive Mode Register	00h	
00081h	U0BRG_0	UART0_0 Bit Rate Register	XXh	
00082h	U0TB_0	UART0_0 Transmit Buffer Register	XXh	
00083h			XXh	
00084h	U0C0_0	UART0_0 Transmit/Receive Control Register 0	00001000b	
00085h	U0C1_0	UART0_0 Transmit/Receive Control Register 1	00000010b	
00086h	U0RB_0	UART0_0 Receive Buffer Register	XXXXh	
00087h				
00088h	U0IR_0	UART0_0 Interrupt Flag and Enable Register	00h	
00089h				
0008Ah				
0008Bh				
0008Ch	LINCR2_0	LIN_0 Special Function Register	00h	
0008Dh				
0008Eh	LINCT_0	LIN_0 Control Register	00h	
0008Fh	LINST_0	LIN_0 Status Register	00h	
00090h	U0MR_1	UART0_1 Transmit/Receive Mode Register	00h	
00091h	U0BRG_1	UART0_1 Bit Rate Register	XXh	
00092h	U0TB_1	UART0_1 Transmit Buffer Register	XXh	
00093h			XXh	
00094h	U0C0_1	UART0_1 Transmit/Receive Control Register 0	00001000b	
00095h	U0C1_1	UART0_1 Transmit/Receive Control Register 1	00000010b	
00096h	U0RB_1	UART0_1 Receive Buffer Register	XXXXh	
00097h				
00098h	U0IR_1	UART0_1 Interrupt Flag and Enable Register	00h	
00099h				
0009Ah				
0009Bh				
0009Ch				
0009Dh				
0009Eh				
0009Fh				
000A0h				
000A1h				
000A2h				
000A3h				
000A4h				
000A5h				
000A8h				
000A9h				
000AAh				
000ABh				
000ACh				
000ADh				
000AEh				
000AFh				
000B0h				
000B1h				
000B4h				
000B5h				
000B8h				
000B9h				

X: Undefined

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.7 SFR Information (7) (1)

Address	Symbol	Register Name	After Reset	Remarks
0017Ah	TREIFR	Timer RE2 Interrupt Flag Register	00h	
0017Bh	TREIER	Timer RE2 Interrupt Enable Register	00h	
0017Ch	TREAMN	Timer RE2 Alarm Minute Register	00h	
0017Dh	TREahr	Timer RE2 Alarm Hour Register	00h	
0017Eh	TREAwK	Timer RE2 Alarm Day-of-the-Week Register	00h	
0017Fh	TREPRC	Timer RE2 Protect Register	00h	
00180h to 001FFh				
00200h	AD0	A/D Register 0	00h	
00201h			00h	
00202h	AD1	A/D Register 1	00h	
00203h			00h	
00204h	AD2	A/D Register 2	00h	
00205h			00h	
00206h	AD3	A/D Register 3	00h	
00207h			00h	
00208h	AD4	A/D Register 4	00h	
00209h			00h	
0020Ah	AD5	A/D Register 5	00h	
0020Bh			00h	
0020Ch	AD6	A/D Register 6	00h	
0020Dh			00h	
0020Eh	AD7	A/D Register 7	00h	
0020Fh			00h	
00210h				
00211h				
00212h				
00213h				
00214h	ADMOD	A/D Mode Register	00h	
00215h	ADINSEL	A/D Input Select Register	11000000b	
00216h	ADCON0	A/D Control Register 0	00h	
00217h	ADCON1	A/D Control Register 1	00h	
00218h				
00219h				
0021Ah				
0021Bh				
0021Ch				
0021Dh				
0021Eh				
0021Fh				
00220h				
00221h				
00222h				
00223h				
00224h				
00225h				
00226h				
00227h				
00228h	INTCMP	Comparator B Control Register 0	00h	
00229h				
0022Ah				
0022Bh				
0022Ch				
0022Dh				
0022Eh				
0022Fh				
00230h	INTEN	External Input Enable Register 0	00h	
00231h	INTEN1	External Input Enable Register 1	00h	
00232h	INTF	INT Input Filter Select Register 0	00h	
00233h	INTF1	INT Input Filter Select Register 1	00h	
00234h	INTPOL	INT Input Polarity Switch Register	00h	
00235h				
00236h	KIEN	Key Input Interrupt Enable Register	00h	
00237h				
00238h	MSTCR0	Module Standby Control Register 0	00h	
00239h	MSTCR1	Module Standby Control Register 1	00h	

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.8 SFR Information (8) (1)

Address	Symbol	Register Name	After Reset	Remarks
0023Ah	MSTCR2	Module Standby Control Register 2	00h	
0023Bh	MSTCR3	Module Standby Control Register 3	00h	
0023Ch	MSTCR4	Module Standby Control Register 4	00h	
0023Dh				
0023Eh				
0023Fh				
00240h				
00241h				
00242h				
00243h				
00244h				
00245h				
00246h				
00247h				
00248h				
00249h				
0024Ah				
0024Bh				
0024Ch				
0024Dh				
0024Eh				
0024Fh				
00250h				
00251h				
00252h	FST	Flash Memory Status Register	10000X00b	
00253h				
00254h	FMR0	Flash Memory Control Register 0	00h	
00255h	FMR1	Flash Memory Control Register 1	00h	
00256h	FMR2	Flash Memory Control Register 2	00h	
00257h				
00258h				
00259h				
0025Ah				
0025Bh				
0025Ch				
0025Dh				
0025Eh				
0025Fh				
00260h	AIADR0L	Address Match Interrupt Address 0L Register	XXXXh	
00261h				
00262h	AIADR0H	Address Match Interrupt Address 0H Register	0000XXXXb	
00263h	AIEN0	Address Match Interrupt Enable 0 Register	00h	
00264h	AIADR1L	Address Match Interrupt Address 1L Register	XXXXh	
00265h				
00266h	AIADR1H	Address Match Interrupt Address 1H Register	0000XXXXb	
00267h	AIEN1	Address Match Interrupt Enable 1 Register	00h	
00268h				
00269h				
0026Ah				
0026Bh				
0026Ch				
0026Dh				
0026Eh				
0026Fh				
00270h				
00271h				
00272h				
00273h				
00274h				
00275h				
00276h				
00277h				
00278h				
00279h				
0027Ah				
0027Bh				
0027Ch				
0027Dh				
0027Eh				
0027Fh				

X: Undefined

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.10 SFR Information (10) ⁽¹⁾

Address	Symbol	Register Name	After Reset	Remarks
002C0h	PUR0	Pull-Up Control Register 0	00h	
002C1h	PUR1	Pull-Up Control Register 1	00h	
002C2h	PUR2	Pull-Up Control Register 2	00h	
002C3h				
002C4h				
002C5h				
002C6h				
002C7h				
002C8h	P1DRR	Port P1 Drive Capacity Control Register	00h	
002C9h	P2DRR	Port P2 Drive Capacity Control Register	00h	
002CAh				
002CBh				
002CCh	DRR0	Drive Capacity Control Register 0	00h	
002CDh	DRR1	Drive Capacity Control Register 1	00h	
002CEh	DRR2	Drive Capacity Control Register 2	00h	
002CFh				
002D0h	VLT0	Input Threshold Control Register 0	00h	
002D1h	VLT1	Input Threshold Control Register 1	00h	
002D2h	VLT2	Input Threshold Control Register 2	00h	
002D3h				
002D4h				
002D5h				
002D6h				
002D7h				
002D8h				
002D9h				
002DAh				
002DBh				
002DCh				
002DDh				
002DEh				
002DFh				
002E0h	PORT0	Port P0 Register	XXh	
002E1h	PORT1	Port P1 Register	XXh	
002E2h	PD0	Port P0 Direction Register	00h	
002E3h	PD1	Port P1 Direction Register	00h	
002E4h	PORT2	Port P2 Register	XXh	
002E5h	PORT3	Port P3 Register	XXh	
002E6h	PD2	Port P2 Direction Register	00h	
002E7h	PD3	Port P3 Direction Register	00h	
002E8h	PORT4	Port P4 Register	XXh	
002E9h	PORT5	Port P5 Register	XXh	
002EAh	PD4	Port P4 Direction Register	00h	
002EBh	PD5	Port P5 Direction Register	00h	
002ECh	PORT6	Port P6 Register	XXh	
002EDh				
002EEh	PD6	Port P6 Direction Register	00h	
002EFh				
002F0h	PORT8	Port P8 Register	XXh	
002F1h				
002F2h	PD8	Port P8 Direction Register	00h	
002F3h				
002F4h				
002F5h				
002F6h				
002F7h				
002F8h				
002F9h				
002FAh				
002FBh				
002FCh				
002FDh				
002FEh				
002FFh				
00300h to 003FFh				

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.11 SFR Information (11) ⁽¹⁾

Address	Symbol	Register Name	After Reset	Remarks
00400h to 053FFh	On-chip RAM	On-chip RAM		
05400h to 069FFh				
06A00h	ELSELR0	Event Output Destination Select Register 0	00h	
06A01h	ELSELR1	Event Output Destination Select Register 1	00h	
06A02h	ELSELR2	Event Output Destination Select Register 2	00h	
06A03h	ELSELR3	Event Output Destination Select Register 3	00h	
06A04h	ELSELR4	Event Output Destination Select Register 4	00h	
06A05h				
06A06h				
06A07h				
06A08h	ELSELR8	Event Output Destination Select Register 8	00h	
06A09h	ELSELR9	Event Output Destination Select Register 9	00h	
06A0Ah				
06A0Bh	ELSELR11	Event Output Destination Select Register 11	00h	
06A0Ch	ELSELR12	Event Output Destination Select Register 12	00h	
06A0Dh	ELSELR13	Event Output Destination Select Register 13	00h	
06A0Eh	ELSELR14	Event Output Destination Select Register 14	00h	
06A0Fh	ELSELR15	Event Output Destination Select Register 15	00h	
06A10h	ELSELR16	Event Output Destination Select Register 16	00h	
06A11h				
06A12h				
06A13h				
06A14h				
06A15h				
06A16h				
06A17h				
06A18h				
06A19h				
06A1Ah				
06A1Bh				
06A1Ch				
06A1Dh				
06A1Eh				
06A1Fh				
06A20h				
06A21h				
06A22h				
06A23h				
06A24h				
06A25h				
06A26h				
06A27h				
06A28h				
06A29h				
06A2Ah				
06A2Bh				
06A2Ch				
06A2Dh				
06A2Eh				
06A2Fh				
06A30h				
06A31h to 06AFFh				

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.14 SFR Information (14) ⁽¹⁾

Address	Symbol	Register Name	After Reset	Remarks
06C4Ah	DTCCT1	DTC Transfer Count Register 1	XXh	
06C4Bh	DTRLD1	DTC Transfer Count Reload Register 1	XXh	
06C4Ch	DTSAR1	DTC Source Address Register 1	XXXXh	
06C4Dh				
06C4Eh	DTDAR1	DTC Destination Address Register 1	XXXXh	
06C4Fh				
06C50h	DTCCR2	DTC Control Register 2	XXh	
06C51h	DTBLS2	DTC Block Size Register 2	XXh	
06C52h	DTCCT2	DTC Transfer Count Register 2	XXh	
06C53h	DTRLD2	DTC Transfer Count Reload Register 2	XXh	
06C54h	DTSAR2	DTC Source Address Register 2	XXXXh	
06C55h				
06C56h	DTDAR2	DTC Destination Address Register 2	XXXXh	
06C57h				
06C58h	DTCCR3	DTC Control Register 3	XXh	
06C59h	DTBLS3	DTC Block Size Register 3	XXh	
06C5Ah	DTCCT3	DTC Transfer Count Register 3	XXh	
06C5Bh	DTRLD3	DTC Transfer Count Reload Register 3	XXh	
06C5Ch	DTSAR3	DTC Source Address Register 3	XXXXh	
06C5Dh				
06C5Eh	DTDAR3	DTC Destination Address Register 3	XXXXh	
06C5Fh				
06C60h	DTCCR4	DTC Control Register 4	XXh	
06C61h	DTBLS4	DTC Block Size Register 4	XXh	
06C62h	DTCCT4	DTC Transfer Count Register 4	XXh	
06C63h	DTRLD4	DTC Transfer Count Reload Register 4	XXh	
06C64h	DTSAR4	DTC Source Address Register 4	XXXXh	
06C65h				
06C66h	DTDAR4	DTC Destination Address Register 4	XXXXh	
06C67h				
06C68h	DTCCR5	DTC Control Register 5	XXh	
06C69h	DTBLS5	DTC Block Size Register 5	XXh	
06C6Ah	DTCCT5	DTC Transfer Count Register 5	XXh	
06C6Bh	DTRLD5	DTC Transfer Count Reload Register 5	XXh	
06C6Ch	DTSAR5	DTC Source Address Register 5	XXXXh	
06C6Dh				
06C6Eh	DTDAR5	DTC Destination Address Register 5	XXXXh	
06C6Fh				
06C70h	DTCCR6	DTC Control Register 6	XXh	
06C71h	DTBLS6	DTC Block Size Register 6	XXh	
06C72h	DTCCT6	DTC Transfer Count Register 6	XXh	
06C73h	DTRLD6	DTC Transfer Count Reload Register 6	XXh	
06C74h	DTSAR6	DTC Source Address Register 6	XXXXh	
06C75h				
06C76h	DTDAR6	DTC Destination Address Register 6	XXXXh	
06C77h				
06C78h	DTCCR7	DTC Control Register 7	XXh	
06C79h	DTBLS7	DTC Block Size Register 7	XXh	
06C7Ah	DTCCT7	DTC Transfer Count Register 7	XXh	
06C7Bh	DTRLD7	DTC Transfer Count Reload Register 7	XXh	
06C7Ch	DTSAR7	DTC Source Address Register 7	XXXXh	
06C7Dh				
06C7Eh	DTDAR7	DTC Destination Address Register 7	XXXXh	
06C7Fh				
06C80h	DTCCR8	DTC Control Register 8	XXh	
06C81h	DTBLS8	DTC Block Size Register 8	XXh	
06C82h	DTCCT8	DTC Transfer Count Register 8	XXh	
06C83h	DTRLD8	DTC Transfer Count Reload Register 8	XXh	
06C84h	DTSAR8	DTC Source Address Register 8	XXXXh	
06C85h				
06C86h	DTDAR8	DTC Destination Address Register 8	XXXXh	
06C87h				
06C88h	DTCCR9	DTC Control Register 9	XXh	
06C89h	DTBLS9	DTC Block Size Register 9	XXh	
06C8Ah	DTCCT9	DTC Transfer Count Register 9	XXh	
06C8Bh	DTRLD9	DTC Transfer Count Reload Register 9	XXh	
06C8Ch	DTSAR9	DTC Source Address Register 9	XXXXh	
06C8Dh				
06C8Eh	DTDAR9	DTC Destination Address Register 9	XXXXh	
06C8Fh				

X: Undefined

Note:

1. The blank areas are reserved. No access is allowed.

Table 3.16 SFR Information (16) ⁽¹⁾

Address	Symbol	Register Name	After Reset	Remarks
06CD0h	DTCCR18	DTC Control Register 18	XXh	
06CD1h	DTBLS18	DTC Block Size Register 18	XXh	
06CD2h	DTCCT18	DTC Transfer Count Register 18	XXh	
06CD3h	DTRL18	DTC Transfer Count Reload Register 18	XXh	
06CD4h	DTSAR18	DTC Source Address Register 18	XXXXh	
06CD5h				
06CD6h	DTDAR18	DTC Destination Address Register 18	XXXXh	
06CD7h				
06CD8h	DTCCR19	DTC Control Register 19	XXh	
06CD9h	DTBLS19	DTC Block Size Register 19	XXh	
06CDAh	DTCCT19	DTC Transfer Count Register 19	XXh	
06CDBh	DTRL19	DTC Transfer Count Reload Register 19	XXh	
06CDC	DTSAR19	DTC Source Address Register 19	XXXXh	
06CDDh				
06CDEh	DTDAR19	DTC Destination Address Register 19	XXXXh	
06CDFh				
06CE0h	DTCCR20	DTC Control Register 20	XXh	
06CE1h	DTBLS20	DTC Block Size Register 20	XXh	
06CE2h	DTCCT20	DTC Transfer Count Register 20	XXh	
06CE3h	DTRL20	DTC Transfer Count Reload Register 20	XXh	
06CE4h	DTSAR20	DTC Source Address Register 20	XXXXh	
06CE5h				
06CE6h	DTDAR20	DTC Destination Address Register 20	XXXXh	
06CE7h				
06CE8h	DTCCR21	DTC Control Register 21	XXh	
06CE9h	DTBLS21	DTC Block Size Register 21	XXh	
06CEAh	DTCCT21	DTC Transfer Count Register 21	XXh	
06CEBh	DTRL21	DTC Transfer Count Reload Register 21	XXh	
06CECh	DTSAR21	DTC Source Address Register 21	XXXXh	
06CEDh				
06CEEh	DTDAR21	DTC Destination Address Register 21	XXXXh	
06CEFh				
06CF0h	DTCCR22	DTC Control Register 22	XXh	
06CF1h	DTBLS22	DTC Block Size Register 22	XXh	
06CF2h	DTCCT22	DTC Transfer Count Register 22	XXh	
06CF3h	DTRL22	DTC Transfer Count Reload Register 22	XXh	
06CF4h	DTSAR22	DTC Source Address Register 22	XXXXh	
06CF5h				
06CF6h	DTDAR22	DTC Destination Address Register 22	XXXXh	
06CF7h				
06CF8h	DTCCR23	DTC Control Register 23	XXh	
06CF9h	DTBLS23	DTC Block Size Register 23	XXh	
06CFAh	DTCCT23	DTC Transfer Count Register 23	XXh	
06CFBh	DTRL23	DTC Transfer Count Reload Register 23	XXh	
06CFCh	DTSAR23	DTC Source Address Register 23	XXXXh	
06CFDh				
06CFEh	DTDAR23	DTC Destination Address Register 23	XXXXh	
06CFFh				
06D00h to 06FFFh				

X: Undefined

Note:

1. The blank areas are reserved. No access is allowed.

Table 4.5 Flash Memory (Program ROM) Characteristics
(V_{cc} = 2.7 V to 5.5 V, T_{opr} = –20°C to 85°C (N version)/–40°C to 85°C (D version),
unless otherwise specified)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽¹⁾		1,000 ⁽²⁾	—	—	times
—	Byte program time (Program and erase endurance ≤ 100 times)		—	—	—	μs
—	Byte program time (Program and erase endurance ≤ 1,000 times)		—	—	—	μs
—	Word program time (Program and erase endurance ≤ 100 times)	T _{opr} = 25°C, V _{cc} = 5.0 V	—	100	200	μs
—	Word program time (Program and erase endurance ≤ 100 times)		—	100	400	μs
—	Word program time (Program and erase endurance ≤ 1,000 times)		—	100	650	μs
—	Block erase time		—	0.3	4	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (N ver.) –40 (D ver.)	—	85	°C
—	Data hold time ⁽⁶⁾	Ambient temperature = 55°C ⁽⁷⁾	20	—	—	year

Notes:

1. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. The data hold time includes time that the power supply is off or the clock is not supplied.
7. The data hold time includes 7,000 hours under an environment of ambient temperature 85°C.

Table 4.6 Flash Memory (Data flash Block A to Block D) Characteristics
(V_{cc} = 2.7 V to 5.5 V, T_{opr} = –20°C to 85°C (N version)/–40°C to 85°C (D version),
unless otherwise specified)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽¹⁾		10,000 ⁽²⁾	—	—	times
—	Byte program time (Program and erase endurance ≤ 1,000 times)		—	160	950	μs
—	Byte program time (Program and erase endurance > 1,000 times)		—	300	950	μs
—	Block erase time (Program and erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (Program and erase endurance > 1,000 times)		—	0.3	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	3 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (N ver.) –40 (D ver.)	—	85	°C
—	Data hold time ⁽⁶⁾	Ambient temperature = 55°C ⁽⁷⁾	20	—	—	year

Notes:

1. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100, 1,000 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. The data hold time includes time that the power supply is off or the clock is not supplied.
7. The data hold time includes 7,000 hours under an environment of ambient temperature 85°C.

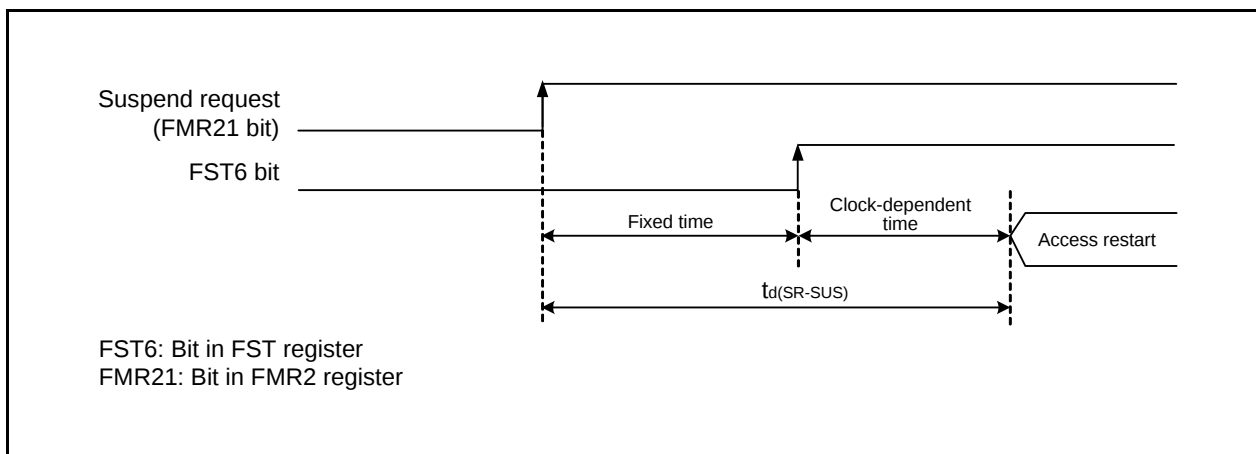


Figure 4.2 Time Delay from Suspend Request until Suspend

Table 4.7 Voltage Detection 0 Circuit Characteristics
**(Measurement conditions: $V_{CC} = 1.8\text{ V to }5.5\text{ V}$, $T_{opr} = -20^{\circ}\text{C to }85^{\circ}\text{C}$ (N version)/
 $-40^{\circ}\text{C to }85^{\circ}\text{C}$ (D version))**

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
Vdet0	Voltage detection level Vdet0_0 ⁽¹⁾	When Vcc falls	1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 ⁽¹⁾	When Vcc falls	2.15	2.35	2.55	V
	Voltage detection level Vdet0_2 ⁽¹⁾	When Vcc falls	2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 ⁽¹⁾	When Vcc falls	3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time ⁽²⁾	At the falling of Vcc from 5 V to (Vdet0 – 0.1) V	—	6	150	μs
—	Voltage detection circuit self power consumption	VCA25 = 1, Vcc = 5.0 V	—	1.5	—	μA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

Notes:

1. The voltage detection level must be selected with bits VDSEL0 and VDSEL1 in the OFS register.
2. Time until the voltage monitor 0 reset is generated after the voltage passes Vdet0.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 4.8 Voltage Detection 1 Circuit Characteristics
(Measurement conditions: Vcc = 1.8 V to 5.5 V, Topr = –20°C to 85°C (N version)/
–40°C to 85°C (D version))

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
Vdet1	Voltage detection level Vdet1_0 ⁽¹⁾	When Vcc falls	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 ⁽¹⁾	When Vcc falls	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 ⁽¹⁾	When Vcc falls	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 ⁽¹⁾	When Vcc falls	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 ⁽¹⁾	When Vcc falls	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 ⁽¹⁾	When Vcc falls	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 ⁽¹⁾	When Vcc falls	2.80	3.10	3.40	V
	Voltage detection level Vdet1_7 ⁽¹⁾	When Vcc falls	2.95	3.25	3.55	V
	Voltage detection level Vdet1_8 ⁽¹⁾	When Vcc falls	3.10	3.40	3.70	V
	Voltage detection level Vdet1_9 ⁽¹⁾	When Vcc falls	3.25	3.55	3.85	V
	Voltage detection level Vdet1_A ⁽¹⁾	When Vcc falls	3.40	3.70	4.00	V
	Voltage detection level Vdet1_B ⁽¹⁾	When Vcc falls	3.55	3.85	4.15	V
	Voltage detection level Vdet1_C ⁽¹⁾	When Vcc falls	3.70	4.00	4.30	V
	Voltage detection level Vdet1_D ⁽¹⁾	When Vcc falls	3.85	4.15	4.45	V
	Voltage detection level Vdet1_E ⁽¹⁾	When Vcc falls	4.00	4.30	4.60	V
	Voltage detection level Vdet1_F ⁽¹⁾	When Vcc falls	4.15	4.45	4.75	V
—	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time ⁽²⁾	At the falling of Vcc from 5 V to (Vdet1 – 0.1) V	—	60	150	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, Vcc = 5.0 V	—	1.7	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

Notes:

1. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 4.9 Voltage Detection 2 Circuit Characteristics
(Measurement conditions: Vcc = 1.8 V to 5.5 V, Topr = –20°C to 85°C (N version)/
–40°C to 85°C (D version))

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
Vdet2	Voltage detection level Vdet2_0	When Vcc falls	3.70	4.00	4.30	V
—	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		—	0.1	—	μs
—	Voltage detection 2 circuit response time ⁽¹⁾	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	—	20	150	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, Vcc = 5.0 V	—	1.7	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽²⁾		—	—	100	μs

Notes:

1. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

4.4 DC Characteristics

Table 4.14 DC Characteristics (1) [4.2 V ≤ V_{CC} ≤ 5.5 V]
(Measurement conditions: V_{CC} = 1.8 V to 5.5 V, Topr = −20°C to 85°C (N version)/
−40°C to 85°C (D version))

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output high voltage	Other than XOUT	Drive capacity is high	I _{OH} = −20 mA	V _{CC} − 2.0	—	V _{CC}	V
			Drive capacity is low	I _{OH} = −5 mA	V _{CC} − 2.0	—	V _{CC}	V
				I _{OH} = −200 μA	V _{CC} − 0.3	—	V _{CC}	V
		XOUT		I _{OH} = −200 μA	1.0	—	V _{CC}	V
V _{OL}	Output low voltage	Other than XOUT	Drive capacity is high	I _{OL} = 20 mA	—	—	2.0	V
			Drive capacity is low	I _{OL} = 5 mA	—	—	2.0	V
				I _{OL} = 200 μA	—	—	0.45	V
		XOUT		I _{OL} = 200 μA	—	—	0.5	V
V _{T+} −V _{T−}	Hysteresis	INT0 to INT4, K10 to K13, TRJIO_0, TRCCLK_0, TRCTRG_0, TRCIOA_0, TRCIOB_0, TRCIOC_0, TRCIOD_0, CLK_0, CLK_1, RXD_0, RXD_1, CTS2, SCL2, SDA2, CLK2, RXD2, SCL_0, SDA_0, SSI_0, SCS_0, SSCK_0, SSO_0			0.1	1.2	—	V
		RESET	V _{CC} = 5.0 V		0.1	1.2	—	V
I _{IH}	Input high current		V _I = 5.0 V		—	—	1.0	μA
I _{IL}	Input low current		V _I = 0 V		—	—	−1.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V		25	50	100	kΩ
R _{FXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R _{FXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Table 4.16 DC Characteristics (3) [$2.7\text{ V} \leq V_{CC} < 4.2\text{ V}$]
**(Measurement conditions: $V_{CC} = 1.8\text{ V}$ to 5.5 V , $T_{opr} = -20^{\circ}\text{C}$ to 85°C (N version)/
 -40°C to 85°C (D version))**

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output high voltage	Other than XOUT	Drive capacity is high	I _{OH} = -5 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity is low	I _{OH} = -1 mA	V _{CC} - 0.5	—	V _{CC}	V
		XOUT		I _{OH} = -200 μ A	1.0	—	V _{CC}	V
V _{OL}	Output low voltage	Other than XOUT	Drive capacity is high	I _{OL} = 5 mA	—	—	0.5	V
			Drive capacity is low	I _{OL} = 1 mA	—	—	0.5	V
		XOUT		I _{OL} = 200 μ A	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	INT0 to INT4, KI0 to KI3, TRJIO_0, TRCCLK_0, TRCTRG_0, TRCIOA_0, TRCIOB_0, TRCIOC_0, TRCIOD_0, CLK_0, CLK_1, RXD_0, RXD_1, CTS2, SCL2, SDA2, CLK2, RXD2, SCL_0, SDA_0, SSI_0, SCS_0, SSCK_0, SSO_0			0.1	0.4	—	V
		RESET	V _{CC} = 3.0 V		0.1	0.5	—	V
I _{IH}	Input high current		V _I = 3.0 V		—	—	1.0	μ A
I _{IL}	Input low current		V _I = 0 V		—	—	-1.0	μ A
R _{PULLUP}	Pull-up resistance		V _I = 0 V		42	84	168	k Ω
R _{FXIN}	Feedback resistance	XIN			—	0.3	—	M Ω
R _{FXCIN}	Feedback resistance	XCIN			—	8	—	M Ω
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Table 4.18 DC Characteristics (5) [$1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$]
**(Measurement conditions: $V_{CC} = 1.8\text{ V}$ to 5.5 V , $T_{opr} = -20^{\circ}\text{C}$ to 85°C (N version)/
 -40°C to 85°C (D version))**

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output high voltage	Other than XOUT	Drive capacity is high	I _{OH} = -2 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity is low	I _{OH} = -1 mA	V _{CC} - 0.5	—	V _{CC}	V
		XOUT		I _{OH} = -200 μ A	1.0	—	V _{CC}	V
V _{OL}	Output low voltage	Other than XOUT	Drive capacity is high	I _{OL} = 2 mA	—	—	0.5	V
			Drive capacity is low	I _{OL} = 1 mA	—	—	0.5	V
		XOUT		I _{OL} = 200 μ A	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	INT0 to INT4, KI0 to KI3, TRJIO_0, TRCCLK_0, TRCTRG_0, TRCIOA_0, TRCIOB_0, TRCIOC_0, TRCIOD_0, CLK_0, CLK_1, RXD_0, RXD_1, CTS2, SCL2, SDA2, CLK2, RXD2, SCL_0, SDA_0, SSI_0, SCS_0, SSCK_0, SSO_0			0.05	0.2	—	V
		RESET	V _{CC} = 2.2 V		0.05	0.2	—	V
I _{IH}	Input high current		V _I = 2.2 V		—	—	1.0	μ A
I _{IL}	Input low current		V _I = 0 V		—	—	-1.0	μ A
R _{PULLUP}	Pull-up resistance		V _I = 0 V		100	200	400	k Ω
R _{FXIN}	Feedback resistance	XIN			—	0.3	—	M Ω
R _{FXCIN}	Feedback resistance	XCIN			—	8	—	M Ω
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

REVISION HISTORY	R8C/36T-A Group Datasheet
------------------	---------------------------

Rev.	Date	Description	
		Page	Summary
0.01	Feb 23, 2011	—	First Edition issued
1.00	Dec 09, 2011	All pages	"Preliminary", "Under development" deleted, "sensor control unit" → "touch sensor control unit"
		2, 3	Tables 1.1 and 1.2 revised
		6	Figure 1.3 "P3_10/CH10" → "P3_1/CH10"
		11	Table 1.8 "Touch sensor control unit" added
		13	2.1 revised
		16, 17, 19 to 22, 24 to 28	Tables 3.1, 3.2, 3.4 to 3.7, 3.9 to 3.13
		32	Table 3.17 revised, Note 2 added
		33 to 56	"4. Electrical Characteristics" added

All trademarks and registered trademarks are the property of their respective owners.